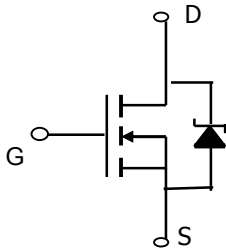
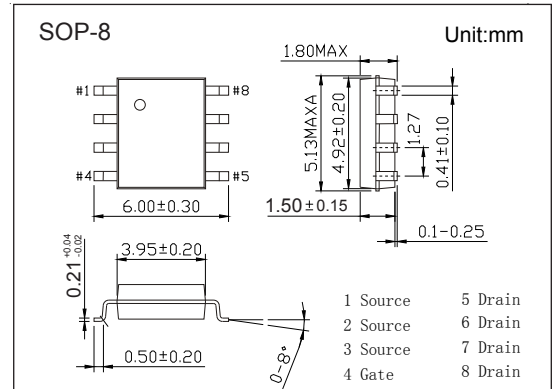


N-Channel MOSFET

AO4724 (KO4724)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 10.5 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 17.5m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 29m\Omega (V_{GS} = 4.5V)$
- SRFET™ Soft Recovery MOSFET: Integrated Schottky Diode



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	10 Sec	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	10.5	7.7	A
	$T_A = 70^\circ\text{C}$		8.5	6.2	
Pulsed Drain Current		I_{DM}	80		
Avalanche Current		I_{AR}	13		
Repetitive Avalanche Energy	$L = 0.3\text{mH}$	E_{AR}	25		mJ
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	3.1	1.7	W
	$T_A = 70^\circ\text{C}$		2	1.1	
Thermal Resistance.Junction- to-Ambient		R_{thJA}	40	75	$^\circ\text{C/W}$
Thermal Resistance.Junction- to-Lead		R_{thJL}	-	24	
Junction Temperature		T_J	150		$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150		

N-Channel MOSFET

AO4724 (KO4724)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250μA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			0.1	mA
		V _{DS} =30V, V _{GS} =0V, T _J =125°C			20	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μ A	1.3		2	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10.5A			17.5	mΩ
		V _{GS} =10V, I _D =10.5A T _J =125°C			25.8	
		V _{GS} =4.5V, I _D =8A			29	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	80			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =10.5A		23		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz		696	900	pF
Output Capacitance	C _{oss}			199		
Reverse Transfer Capacitance	C _{rss}			81		
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.2	1.8	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =10.5A		12.4	16	nC
Total Gate Charge (4.5V)				6.1	8	
Gate Source Charge	Q _{gs}			2.04		
Gate Drain Charge	Q _{gd}			2.7		
Turn-On DelayTime	t _{d(on)}			2.6		
Turn-On Rise Time	t _r	V _{GS} =10V, V _{DS} =15V, R _L =1.43Ω, R _{GEN} =3Ω		6.8		ns
Turn-Off DelayTime	t _{d(off)}			17		
Turn-Off Fall Time	t _f			3.6		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10.5A, di/dt= 300A/us		20.2	26	nA
Body Diode Reverse Recovery Charge	Q _{rr}			7.9		
Maximum Body-Diode Continuous Current	I _S				4.8	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			0.5	V

Note. The static characteristics in Figures 1 to 6 are obtained using <300 us pulses, duty cycle 0.5% max.

■ Marking

Marking	4724 KC****
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N-Channel MOSFET AO4724 (KO4724)

■ Typical Characteristics

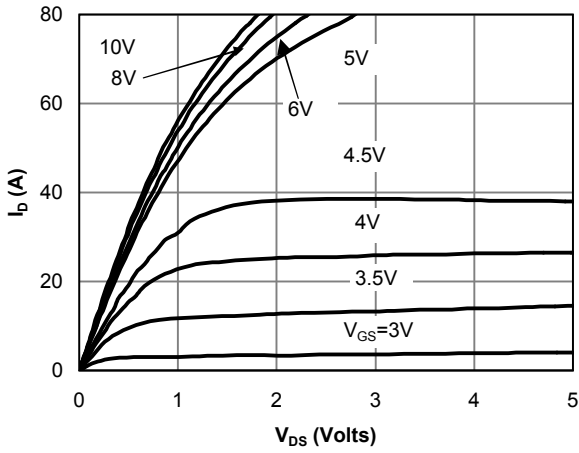


Fig 1: On-Region Characteristics

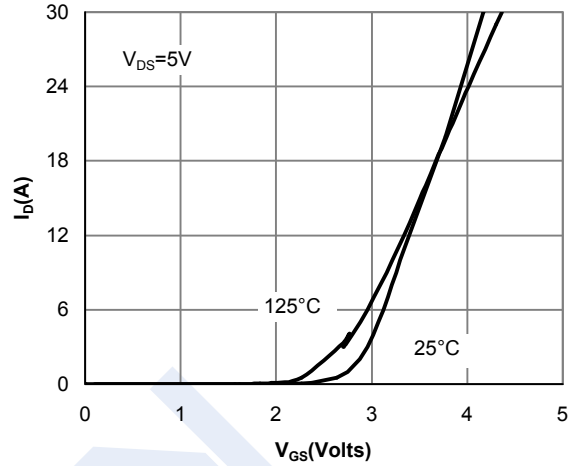


Figure 2: Transfer Characteristics

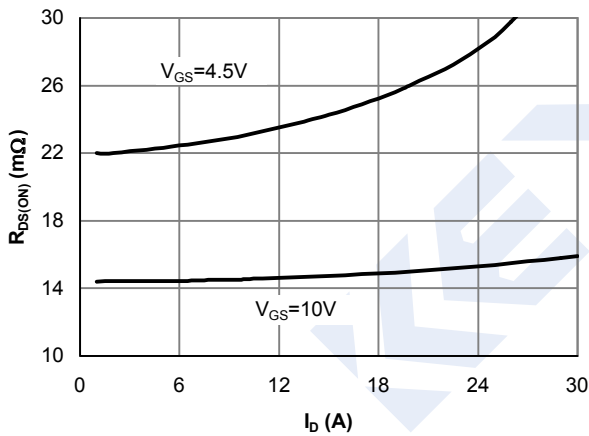


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

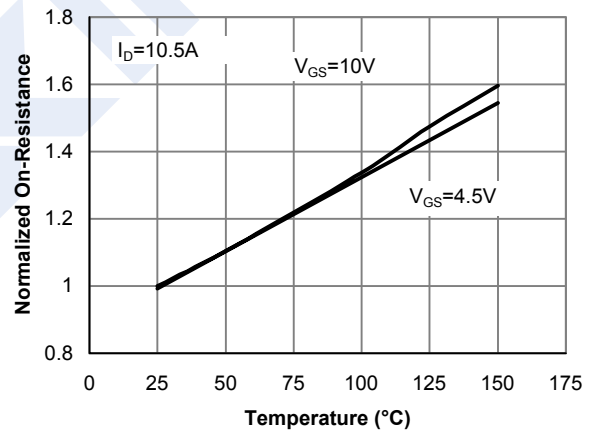


Figure 4: On-Resistance vs. Junction Temperature

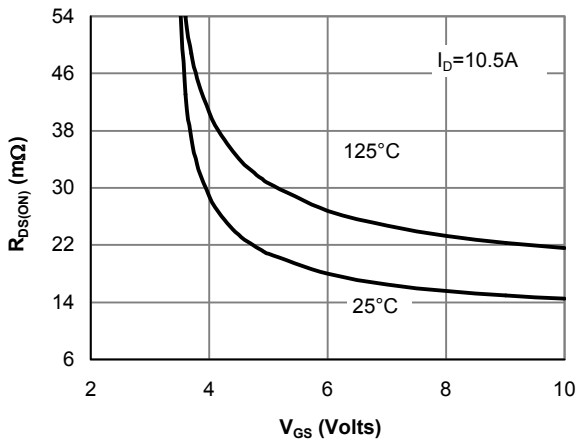


Figure 5: On-Resistance vs. Gate-Source Voltage

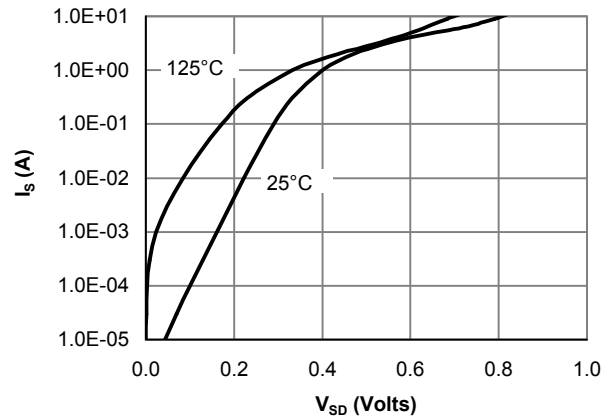


Figure 6: Body-Diode Characteristics

N-Channel MOSFET

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Typical Characteristics

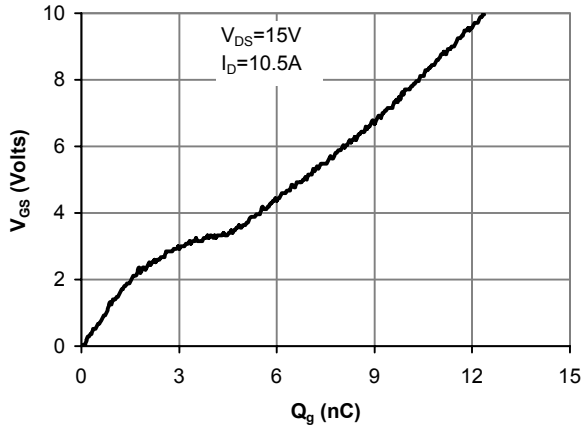


Figure 7: Gate-Charge Characteristics

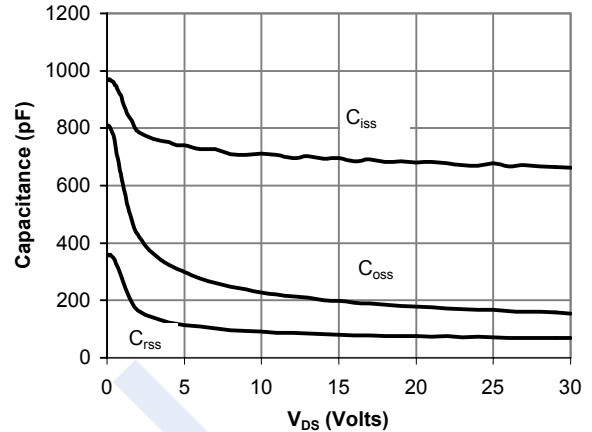


Figure 8: Capacitance Characteristics

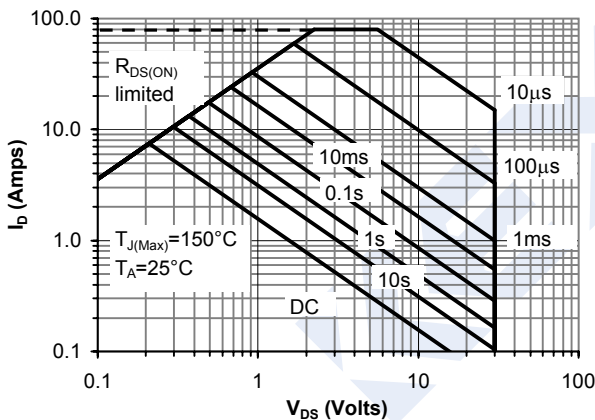


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

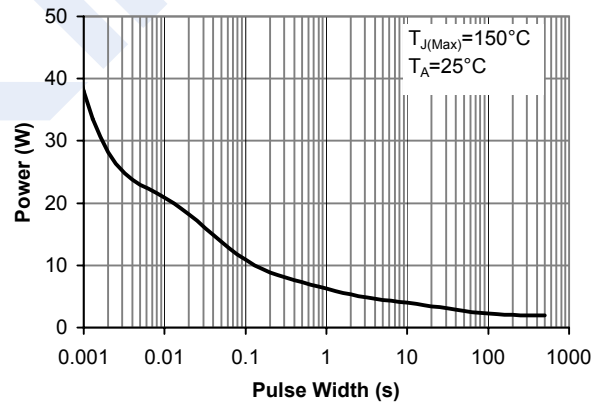


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

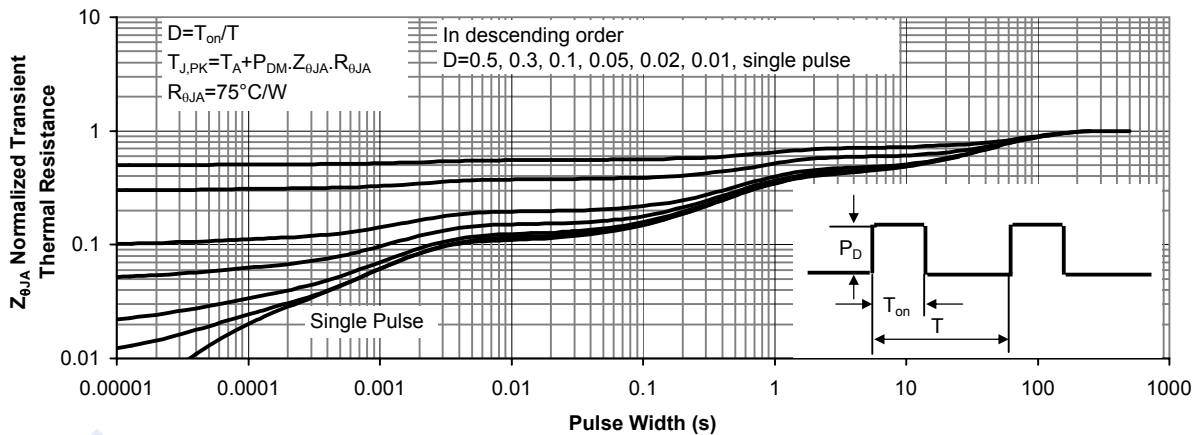


Figure 11: Normalized Maximum Transient Thermal Impedance